

Please note that all claims currently pending and under consideration in the referenced application are shown below. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-34. (Canceled)

35. (Withdrawn) A structure including:
a first layer of silicon-based material;
a first line disposed over the silicon-based material, the first line comprising chromium;
a second line disposed over the first line, the second line comprising aluminum.

36. (Withdrawn) A structure according to claim 35, further including a third line disposed over the second line, the third line comprising chromium.

37. (Withdrawn) A structure according to claim 36, further including a second layer of silicon-based material disposed over the third line.

38. (Previously Presented) An integrated circuit including a first layer of material comprising silicon, a second layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed between the first and second layers of material, the conductor including a first part and a second part, the first part comprising chromium, the second part comprising aluminum, the first part being wrapped around the second part.

39. (Canceled)

40. (Canceled)

41. (Withdrawn) A structure including:
a first layer of material comprising silicon;
a conductor including a first line and a second line, the first line comprising a first conductive material, the second line comprising a second conductive material, the first line being disposed between the second line and the first layer of material.
42. (Withdrawn) A structure according to claim 41, further including a third line disposed over the second line, the third line comprising the first conductive material.
43. (Withdrawn) A structure according to claim 42, further including a second layer of material comprising silicon disposed over the third line.
44. (Withdrawn) A structure according to claim 41, wherein the first conductive material comprises chromium.
45. (Withdrawn) A structure according to claim 41, wherein the second conductive material comprises aluminum.
46. (Withdrawn) A structure according to claim 41, wherein the second conductive material comprises copper.

47. (Previously Presented) An integrated circuit including a first layer of material comprising silicon, a second layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed between the first and second layers of material, the conductor including a first part and a second part, the first part comprising a first conductive material, the second part comprising a second conductive material, the first part being wrapped around the second part.

48. (Original) A circuit according to claim 47, wherein the first conductive material comprises chromium.

49. (Original) A circuit according to claim 47, wherein the second conductive material comprises aluminum.

50. (Original): A circuit according to claim 47, wherein the second conductive material comprises copper.

51. (Previously Presented) An integrated circuit including a layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed adjacent to the first layer of material, the conductor including a first part and a second part, the first part comprising a first conductive material, the second part comprising a second conductive material, the first part being wrapped around the second part.

52. (Original) A circuit according to claim 51, wherein the first conductive material comprises chromium.

53. (Original) A circuit according to claim 51, wherein the second conductive material comprises aluminum.

54. (Original) A circuit according to claim 51, wherein the second conductive material comprises copper.

55. (Previously Presented) An integrated circuit including a multiplicity of devices and a network of conductors electrically connecting selective ones of the devices, the devices and the conductors being disposed in a material comprising silicon, each conductor in the network comprising a first conductive material and a second conductive material, the first conductive material being wrapped around the second conductive material and preventing the second conductive material from contacting the material comprising silicon.

56. (Original) A circuit according to claim 55, wherein the first conductive material comprises chromium.

57. (Original) A circuit according to claim 55, wherein the second conductive material comprises aluminum.

58. (Original) A circuit according to claim 55, wherein the second conductive material comprises copper.